

Attorney's Docket No. 005819.P001

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of:

Jack Zezhong Peng

Application No.: New Application

Filed: Herewith

For: SEMICONDUCTOR MEMORY
CELL AND MEMORY ARRAY
USING A BREAKDOWN PHENOMENA
IN AN ULTRA-THIN DIELECTRIC

Examiner: Not Yet Assigned

Art Unit: Not Yet Assigned



Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with copies of the documents cited on that form. It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

Pursuant to 37 C.F.R. § 1.97, this Information Disclosure Statement is being submitted under one of the following (as indicated by an "X" to the left of the appropriate paragraph):

XXX 37 C.F.R. §1.97(b).

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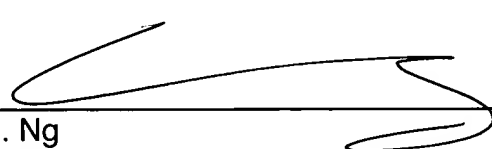
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If there are any additional charges, please charge Deposit Account No.
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Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: 9/18, 2001



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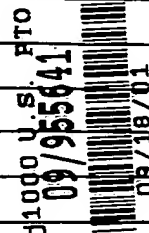
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				Application Number	New Application
				Filing Date	Herewith
				First Named Inventor	Jack Zezhong Peng
				Group Art Unit	Not yet assigned
				Examiner Name	Not yet assigned
Sheet	1	of	1	Attorney Docket Number 005819.P001	



U.S. PATENT DOCUMENTS					
Examiner Initials *		U.S. Patent Document Number	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Filing Date if Appropriate

FOREIGN PATENT DOCUMENTS							
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OTHER DOCUMENTS		
Examiner Initials *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published (if known).	Translation? Yes/No
	✓ MIRANDA, ENRIQUE et al; Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO2 Films; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001	
	✓ LOMBARDO, S. et al; Softening of Breakdown in Ultra-Thin Gate Oxide nMOSFET's at Low Inversion Layer Density; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001	
	✓ WU, E.W. et al; Voltage-Dependent Voltage-Acceleration of Oxide Breakdown for Ultra-Thin Oxides; IEEE, 2000.	
	✓ RASRAS, MAHMOUD et al; Substrate Hole Current Origin After Oxide Breakdown; IEEE, 2000.	
	SUNE, JORDI et al.; Post Soft Breakdown Conduction in SiO2 Gate Oxides; IEEE, 2000.	

Examiner Signature	Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.